Amendments to the Claims:

This listing of claims will replace all prior version and listings of claims in the application:

Listing of Claims:

1. (Currently amended) A semiconductor device, comprising:

a trench formed in a substrate;

a diffusion region surrounding the trench to form a buried plate;

a first conductive material formed in the trench, wherein the first conductive material comprises ~~a~~ at least one pillar extending from a bottom of the trench, wherein the first conductive material contacts the buried plate along an entire bottom portion of the trench and along a lower portion of the sidewalls of the trench, and wherein the first conductive material and the buried plate form a first electrode;

a second conductive material disposed in the trench to form a second electrode; and

a node dielectric layer formed between the first electrode and the second electrode.

2. (Currently amended) The semiconductor device as recited in claim 1, wherein the first conductive material ~~is formed into~~ comprises a plurality of pillars extending from the bottom of the trench.

3. (Currently amended) The semiconductor device as recited in claim 2, wherein ~~the plurality of pillars includes~~ a portion of the second conductive material is disposed between the plurality of pillars.

4. (Original) The semiconductor device as recited in claim 1, wherein the first conductive material includes one of a doped polysilicon and a doped amorphous silicon.

5. (Original) The semiconductor device as recited in claim 1, wherein the second conductive material includes doped amorphous silicon.

6. (Currently amended) The semiconductor device as recited in claim 1, wherein a portion of the second conductive material is disposed between the first conductive material and the buried plate.

7-17. (Canceled).

18. (Currently amended) A semiconductor device, comprising:

a trench formed in a substrate;

a diffusion region surrounding the trench to form a buried plate;

a first conductive material formed in the trench, wherein the first conductive material comprises a ~~pillar~~ plurality of pillars extending from a bottom of the trench, wherein the first conductive material contacts the buried plate along an entire bottom portion of the trench and along a lower portion of the sidewalls of the trench, and wherein the first conductive material and the buried plate form a first electrode;

a second conductive material disposed in the trench to form a second electrode; and

a node dielectric layer formed between the first electrode and the second electrode.

19. (Currently amended) The semiconductor device as recited in claim ~~7~~ 18, wherein the first conductive material is formed into ~~a~~ the plurality of pillars extending from the bottom of the trench.

20. (Currently amended) The semiconductor device as recited in claim ~~8~~ 19, wherein the plurality of pillars includes the second conductive material disposed between the plurality of pillars.

21. (Currently amended) The semiconductor device as recited in claim ~~7~~ 18, wherein the first conductive material includes one of a doped polysilicon and a doped amorphous silicon.

22. (Currently amended) The semiconductor device as recited in claim ~~7~~ 18, wherein the second conductive material includes doped amorphous silicon.

23. (Currently amended) The semiconductor device as recited in claim ~~7~~ 18, wherein the second conductive material is disposed between the first conductive material and the buried plate.